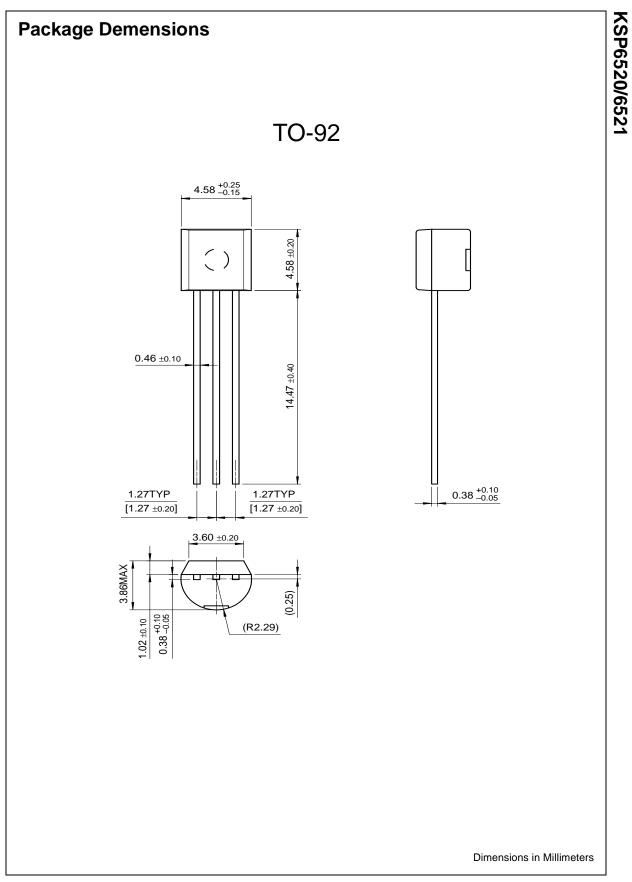


Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	4	V
С	Collector Current	100	mA
°c	Collector Power Dissipation	625	mW
Г <sub>Ј</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

# Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typl	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =0.5mA, I <sub>B</sub> =0	25			V
BV <sub>EBO</sub>	Emitter Base Breakdown Voltage	I <sub>C</sub> =10, I <sub>C</sub> =0	4			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =30V, I <sub>E</sub> =0 V <sub>CE</sub> =20V, I <sub>E</sub> =0			50 50	nA nA
h <sub>FE</sub>	DC Current Gain : KSP6520 : KSP6521 : KSP6520 : KSP6521	I <sub>C</sub> =100μA, V <sub>CE</sub> =10V I <sub>C</sub> =2mA, V <sub>CE</sub> =10V	100 150 200 300		400 600	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.5	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0 f=100KHz			3.5	pF
NF	Noise Figure	I <sub>C</sub> =10μA, V <sub>CE</sub> =5V R <sub>S</sub> =10KΩ f=10Hz to 10KHz			3	dB

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#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSP6520BU	Full Production	\$0.045	<u>TO-92</u>	3	BULK

\* 1,000 piece Budgetary Pricing

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSP6521BU	Full Production	\$0.045	<u>TO-92</u>	3	BULK
KSP6521NBU	Full Production	\$0.045	<u>TO-92</u>	3	BULK

\* 1,000 piece Budgetary Pricing

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